

Amendments to the Specification:

Please replace the "Title of the Invention" with the following amended "Title of the Invention":

~~METHODS OF FABRICATING VERTICAL CARBON NANOTUBE FIELD EFFECT TRANSISTORS FOR ARRANGEMENT IN ARRAYS AND FIELD EFFECT TRANSISTORS AND ARRAYS FORMED THEREBY~~

Please replace the "Abstract of the Disclosure" with the following amended "Abstract of the Disclosure":

~~A method for forming carbon~~ Carbon nanotube field effect transistors, arrays of carbon nanotube field effect transistors, ~~[[and]]~~ device structures, and arrays of device structures ~~formed by the methods. The methods include forming a~~ A stacked device structure including includes a gate electrode layer and catalyst pads each coupled electrically with a source/drain contact. The gate electrode layer is divided into multiple gate electrodes and at least one semiconducting carbon nanotube is synthesized by a chemical vapor deposition process on each of the catalyst pads. ~~The completed device structure includes a gate electrode~~ [[with]] has a sidewall covered by a gate dielectric and at least one semiconducting carbon nanotube adjacent to the sidewall of the gate electrode. Source/drain contacts are electrically coupled with opposite ends of the semiconducting carbon nanotube to complete the device structure. Multiple device structures may be configured either as a memory circuit or as a logic circuit.

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Amendment and Response dated January 18, 2006
Reply to Office Action of November 3, 2005
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